

SS12F THRU SS120F

PINNING

PIN

1

2

Surface Mount Schottky Barrier Rectifier

Reverse Voltage - 20 to 200 V

Forward Current - 1.0 A

DESCRIPTION

Cathode

Anode

Marking Code: SS12 - SS120

Simplified outline SMAF and symbol

FEATURES

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

• Case: SMAF

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 27mg 0, 00086oz

Approx. Weight. 27mg 0. 0000002	,									
Absolute Maximum Ratings and I	Electrical	l charac	teristics							
Ratings at 25 °C ambient temperature unless	otherwise	specified.	Single pha	ise, half w	ave, 60Hz	z resistive	or inductiv	ve load,		
for capacitive load, derate by 20 %										
Parameter	Symbols	SS12F	SS14F	SS16F	SS18F	SS110F	SS112F	SS115F	SS120F	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	٧
Maximum Average Forward Rectified Current	I _{F(AV)}				1	.0				А

	Y 00	20		00	00	100	120	100	200	(W)))
Maximum Average Forward Rectified Current	I _{F(AV)}				1	.0			А	
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	IFSM		4	10			3	0		А
Max Instantaneous Forward Voltage at 1 A	V _F	0.5	5	0.	70	0.	85	0.	90	V
Maximum DC Reverse Current T _a = 25°C at Rated DC Reverse Voltage T _a =100°C	I _R	0		.3		Track of	0.2 5 0.1 2		.1 2	mA
Typical Junction Capacitance 13	Cj	11 (110 80					pF		
Typical Thermal Resistance 2)	R _{BJA}	115							°C/W	
Operating Junction Temperature Range	T _i	-55 ~ +125						°C		

¹⁾ Measured at 1MHz and applied reverse voltage of 4 V D.C.

-55 ~ +150

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Storage Temperature Range

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²⁾ P.C.B. mounted with 0.2 X 0.2" (5 X 5 mm) copper pad areas.



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Fig.1 Forward Current Derating Curve

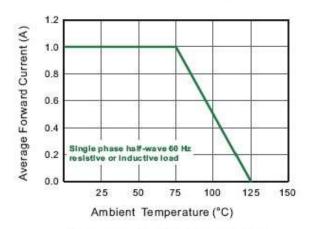


Fig.3 Typical Forward Characteristic

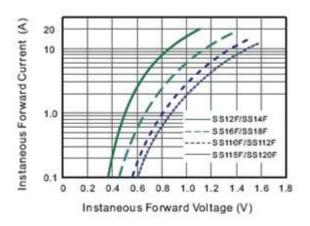


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

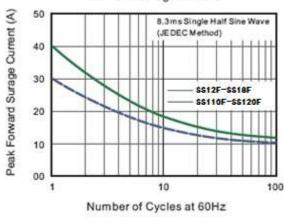


Fig.2 Typical Reverse Characteristics

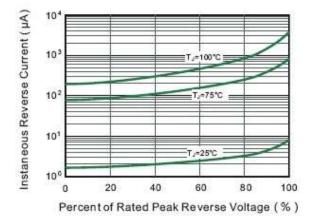


Fig. 4 Typical Junction Capacitance

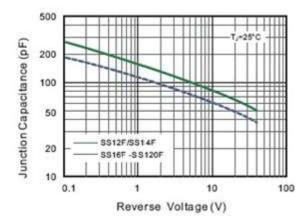
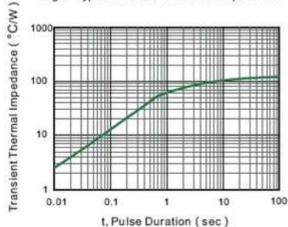


Fig.6- Typical Transient Thermal Impedance



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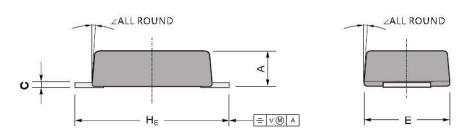


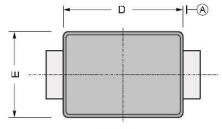
SS12F THRU SS120F

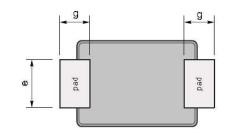
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SMAF





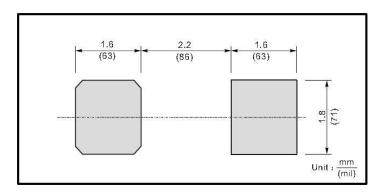


Top View

Bottom View

UNIT		Α	O	D	Ш	Ф	9	H⊨	Z
mm	max	1.1	0.20	3.7	2.7	1.6	1.2	4.9	
	min	0.9	0.12	3.3	2.4	1.3	8.0	4.4	7°
mil	max	43	7.9	146	106	63	47	193	Ţ.
11111	min	35	4.7	130	94	51	31	173	

The recommended mounting pad size



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